

Functionalization mediates heat transport in graphene nanoflakes

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Abstract

Self-heating is a severe problem for high-power microelectronic devices. Graphene and few-layer graphene have attracted tremendous attention for heat removal thanks to their extraordinarily high in-plane thermal conductivity. However, this high thermal conductivity undergoes severe degradations caused by the contact with the substrate and the functionalization-induced point defects. Here we show that thermal management of a micro heater can be substantially improved via introduction of alternative heat-escaping channels implemented with graphene-based film covalently bonded to functionalized graphene oxide through silane molecules. Theoretical and experimental results demonstrate a counter-intuitive enhancement of the thermal conductivity of such a graphene-based film. This increase in the in-plane thermal conductivity of supported graphene is accompanied by an improvement on the graphene-substrates thermal contact. Using infrared thermal imaging, we demonstrate that the temperature of the hotspots can be lowered by 12°C in transistors operating at 130 W mm^{-2} , which corresponds to half of an order-of-magnitude increase in the device lifetime. Ab initio and molecular dynamics simulations reveal that the functionalization constrains the cross-plane scattering of low frequency phonons, which in turn enhances in-plane heat conduction of the bonded graphene film by recovering the long flexural phonon lifetime.

INTRODUCTION

Anisotropic properties of two-dimensional (2D) layered materials make them promising in the application of next generation electronic device. Graphene and few-layer graphene (FLG) have been most intensely studied for thermal management, due to their extraordinarily high in-plane thermal conductivity (κ) [1–4]. However, in most practical applications, graphene/FLG will be supported by and integrated with insulators, both in un electronic circuitry and heat-spreader applications [5]. Therefore, thermal energy flow will be limited both by the in-plane thermal conductivity (κ) of the supported graphene/FLG and by the thermal boundary resistance (R) at the graphene/FLG-substrate interface [6].

Due to the exceedingly large surface-to-volume ratio, κ is very sensitive to the interactions with the environment. Indeed, when supported on an amorphous substrate, κ of the suspended graphene decreased by almost one order of magnitude, from $\sim 4000 \text{ Wm}^{-1}\text{K}^{-1}$ [7] to $\sim 600 \text{ Wm}^{-1}\text{K}^{-1}$ [8]. Such a striking reduction in κ significantly limits the thermal performance of graphene/FLG in real applications and arises from the strong scattering of the important heat carrying flexural acoustic (ZA) modes [9] to the substrate [10]. More specifically, it was identified that the phonon relaxation times (RTs) of graphene ZA modes are suppressed when supported on a SiO_2 substrate. It was suggested that suitably choosing the substrate material [8] and modulating its coupling to graphene [6] may be useful to improve κ of the supported graphene/FLG.

The thermal boundary resistance (R) of a graphene/FLG-substrate interface is another limiting factor to their thermal performance in devices. Covalent functionalization has been proven to efficiently promote heat transfer between interfaces by introducing additional thermal pathways through the functionalizing molecules [11–26]. For example, self-assembled-monolayers (SAM) were used to functionalize metallic surfaces to enhance heat transport across metal-water [13, 20], metal-gas [21], metal-semiconductor [14] and metal-polymer [24] interface. Functionalization was used in graphene and CNT nanocomposites to mitigate the high thermal boundary resistance between the graphene/CNT fillers and the polymer matrices [11, 18, 19, 23]. Functionalized molecules help align and densely pack multilayer graphene sheets and reduce the interlayer thermal resistance of graphene [18]. Recently, it was shown that plasma-functionalized graphene was shown to increase the cross-plane thermal conductance between aluminum and its substrate by a factor of two [12]. Neverthe-

less, the functionalization-introduced point defects will further decrease κ of the supported graphene/FLG, as they introduce phonons scattering centers [18, 25, 26].

To make progress, a robust solution that maintains the high thermal conductivity of graphene/FLG when supported, while effectively reducing the thermal interface resistance is needed. In this study, we theoretically and experimentally investigate the basal-plane thermal conductivity and membrane-substrate thermal resistance of graphene film covalently linked to a silane-functionalized graphene oxide (FGO) support (figure 1). Intuitively, we might expect that attaching a molecule to a graphene surface would increase phonon scattering and reduce κ . We report here a counter-intuitive increase of κ in the supported graphene films with silane functionalization. We attribute this unexpected phenomenon to the silane functionalization, which mediates the graphene film-FGO substrate scattering and recovers the long graphene ZA modes relaxation time. Our model demonstrates that with a large number density ρ of molecules, the overall in-plane thermal conductivity κ of the graphene-based film is enhanced by $\sim 15\%$ with the presence of the FGO substrate, whereas its thermal resistance R with the substrate falls below that without the functionalization. Both phenomena indicate that graphene film-silane-FGO structures is a useful tool for optimizing thermal management.

RESULT AND DISCUSSION

A graphene membrane bonded to the FGO substrate through silane molecules is shown in Figure 1(a) and (b). To synthesize experimentally a graphene-based film and FGO (figure 1c), we first prepared a graphene oxide (GO) dispersion (See Experimental Section). The FGO was obtained by functionalizing GO with a silane-based chemistry suitable for reactive oxide-forming surfaces including the basal plane of GO and SiO_2 . Silane is widely used as a coupling agent to improve the adhesion performance of the interfaces. The FGO layer has a thickness of ~ 5 nm. The graphene film was obtained after chemical reduction of the GO. The graphene film was then spin-coated [27] with the FGO and the resulting bundle was transferred to a thermal evaluation device [28], resulting in the formation of molecular bridges between the graphene surface and the device’s SiO_2 substrate. The thermal evaluation device was integrated with micro Pt-based heating resistors as the hot spot and temperature sensors [28], acting as a simulation platform of an electronic component to

demonstrate the heat-spreading capability of the supported graphene film. Fig. 1(c) shows the temperature measured in situ at the hot spot and compares the thermal performance of the graphene-film with and without the functionalization. With a constant heat flux of 1300 W cm^{-2} at the Pt hot spot, the temperature at the hot spot decreased from $\sim 146^\circ\text{C}$ to $\sim 140^\circ\text{C}$ ($\Delta T \approx 6^\circ\text{C}$) with the graphene film only as heat spreader. In contrast, by chemically bonding the graphene film to the FGO substrate, the hot spot was cooled down from $\sim 146^\circ\text{C}$ to $\sim 134^\circ\text{C}$ ($\Delta T \approx 12^\circ\text{C}$). The heat-spreading performance is thus enhanced by $\sim 50\%$. We have implemented a finite-element (FEM) model (See Section V in [29]) of the heat spreading device by taking the results of atomistic simulation as input parameters. As shown in Figure 1(c), the heat-spreading performance of the equivalent macroscopic FEM model agrees reasonably well with the one measured by experiments.

To explore the physics behind this counter-intuitive increase of κ in the supported graphene film with silane functionalization, we first performed molecular dynamic (MD) simulations to study a nanoscale molecular junction between two stacks of multi-layer graphene nanoflakes. We replaced the graphene oxide by pristine graphene for the simplification of computation. This simplification is relevant since the oxidation of substrate has a minor impact on the in-plane and cross-plane thermal transport in the supported graphene-based film which we are interested in. We consider defect-free and isotopically pure graphene flakes of $10 \times 10 \text{ nm}^2$ thermalized at 300 K (See methods and [29] Section I). The FGO substrate has a 5 nm thickness as in the experiments. Conventional silica substrate results in a substantial decrease of the basal-plane thermal conductivity of graphene due to the non-conformality of the substrate-graphene interface [8]. For the sake of comparison, the FGO substrate proposed herein minimizes the perturbation of substrate on the morphology of graphene (see Fig. 1(c)), thus maintaining its high thermal conductivity. Periodic boundary conditions were used in the in-plane directions so that the MD system corresponds to two thin films connected through silane molecules with the number density ρ , defined as the number of molecules per graphene unit area.

To illustrate the intriguing role of the functionalizing molecule, the in-plane thermal conductivity κ of the film and its interfacial thermal resistance R [29] (Supplemental Information Section I) with the FGO substrate from MD simulation combined with linear response theory is plotted as a function of the graphene layer number l_G in the film in Figure 2 (a) and (b), respectively. First a supercell containing a single molecule is studied, which corresponds

to $\rho = 0.081 \text{ nm}^{-2}$. For $l_G \geq 2$, the presence of the molecule results in an unexpected increase both in the graphene film thermal conductivity κ and in R . An overall decaying trend of the in-plane thermal conductivity κ of the graphene film and its resistance R with the substrate versus the layer number l_G is observed until the value of bulk graphite is approached. This is due to the increased cross-plane coupling of the low-energy phonons. A similar decay was found both in experimental measurements of κ [7] of suspended graphene and in simulation-based estimates of R [30]. Unlike silica-supported graphene[8], the few-layer graphene on a functionalized graphene oxide support recovers the high thermal conductivity and follow the same decaying trend versus l_G as the suspended graphene [7]. Therefore the proposed FGO substrate maintains the high thermal conductivity of graphene compared to a silica substrate. For $l_G = 1$, the presence of the molecule reduces κ , in contrast to the case where no molecule interconnects the graphene film and the substrate. This breakdown of the thermal conductivity enhancement is due to a saddle-like surface generated around the molecule's chemical bonds of amino and silano groups connecting the graphene, with the bond center as the saddle point, as shown in the inset A of Figure 2 (a). The saddlelike surface strongly scatters the ZA phonons, thus decreasing κ of the graphene film. Such a curved surface is common in defective graphene [31, 32], resulting from the Jahn-Teller effect to lower the energy by geometrical distortion [33]. The thermal conductance of a single silane molecule is determined to be 82 pW K^{-1} through the molecular footprint [29] (Supplemental Information Section VI). Our simulated result is comparable to recent measurements of the thermal conductance of alkane thiols SAM at a silica-gold interface[38].

We investigate the microscopic origin of the thermal conductivity κ enhancement in the graphene film by probing the mode-wise phonon relaxation time (RT) [29] (Supplemental Information Section III). The phonon RT τ measures the temporal response of a perturbed phonon mode to relax back to equilibrium due to the net effect of different phonon scattering mechanisms. τ can be defined as [34–36] $\partial n / \partial \tau = (n - n_0) / \tau$ where n and n_0 are the phonon occupation numbers out of and at thermal equilibrium. Under the single-mode-relaxation-time approximation, the thermal conductivity is defined by $\kappa = 1/3 \sum_i C_i v_i^2 \tau_i$ where C_i and v_i are the specific heat per volume unit and the group velocity of the i -th phonon mode. The phonon dispersion of the supported graphene film for $\rho = 0.081 \text{ nm}^{-2}$ and $l_G=2$ and the extracted RT τ for all the phonon modes at 300 K are shown in Figure 3. By inserting the molecule, the RT of the acoustic flexural modes τ_{ZA} largely increases at low frequencies

($\omega < 10$ THz) whereas the longitudinal and transverse modes undergo a slight decrease in $\tau_{LA,LO,TA,TO}$. The notable increase in τ_{ZA} accounts for the enhancement in κ of the graphene film bonded to the substrate since the ZA modes contribute considerably to κ as much as 77% at 300 K [9]. We attribute the increase in τ_{ZA} to the weakened coupling between the graphene film and the substrate, which is reflected by the increased thermal resistance R for $\rho = 0.081 \text{ nm}^{-2}$ and $l_G \geq 2$, as is shown in Fig. 2(b). An approximate expression from the perturbation theory for the RT due to phonon leakage towards the contact interface yields $\tau^{-1} \propto g(\omega)K^2/\omega^2$, where $g(\omega)$ depends on the phonon density of states and K is the average van der Waals (vdW) coupling constant between the graphene film and its substrate. A previous calculation [10] shows that K_{ZA} largely depends on the substrate morphology. The presence of the molecule strongly decreases the film-substrate coupling K_{ZA} , thus yielding a longer time τ_{ZA} . This demonstrates that the silane molecules constrain the film-substrate phonon scattering, which in turn enhances in-plane heat conduction in the bonded graphene film. Note that ZA mode becomes “massive” as shown in Fig. 3(a), i.e., the ZA branch does not reach all the way to zero frequency but shifts to higher frequencies. This might reduce the thermal conductivity, but the effect is weaker than that of the reduced plane-plane scattering, so the in-plane thermal conductivity increases after all.

For heat transport along short molecules such as silane, the internal vibrational properties of the molecule are crucial [38]. To gain a microscopic insight into the thermal transport at the graphene film-substrate interface mediated by the functionalizing molecule, we investigated how the differences in the phonon transmission impact the interfacial phonon transport. To this aim, we probed the phonon transmission $\Xi(E_{\text{ph}})$ by an atomistic Green’s Function (AGF) technique[29] (Supplemental Information Section II) to characterize the local heat conduction with and without the presence of the molecule. $\Xi(E_{\text{ph}})$ enables a precise measurement of the atomic-scale molecule-graphene heat transport that the conventional models like AMM [39] and DMM [40] fail to provide. As shown in Figure 4, the transmission function $\Xi(E_{\text{ph}})$ for the two adjacent graphene layers without any molecule displays a clear stepwise structure that follows the number of open phonon channels. Low energy phonons ($E_{\text{ph}} \leq 10$ meV) dominate heat conduction since the adjacent graphene flakes interact only through weak vdW forces that inhibit the transmission of high-frequency phonons[41]. When the graphene layers are bridged by a silane molecule, the high-frequency phonons act as the major contributors in the heat conductance G_{ph} , creating more phonon channels through

the covalent bond vibrations. This is in line with the transmission calculation of Segal *et al.* [42] who observed a contribution to heat conduction by higher-frequency phonons within the molecule coupled to the low-frequency phonons responsible for heat transport in the thermal reservoirs. The oscillations in the transmission spectrum may originate from phonon interferences within the alkane chain [43–46]. Fabry-Pérot (FP) like interference effects occur in the frequency region of $E_{\text{ph}} = 20 \sim 100$ meV, as was previously observed in an alkane SAM interface [43]. Such FP like interferences originate from the multiple reflected phonons interfering constructively within the alkane chain, as the local maxima in the transmission (Figure 4) through the molecule can attain the same intensity of that through pristine graphene films at given frequencies. Although destructive quantum interference was believed unlikely to occur in a linear alkane chain [44], we observe strong destructive interference patterns in the high frequency range ($\omega = 40 \sim 60$ THz), which may correspond to two-path destructive phonon interferences [45].

We investigated the inter-layer electron transport in the graphene and the effect of the silane intercalation in such a hybrid nanostructure through a density-functional-theory calculation combined with Green’s function (Methods). As shown in Fig. 4 (c) and (d), the presence of the molecule reduces the electron transmission by interrupting the $\pi - \pi$ stacking of the phenyl rings in the adjacent graphene flakes. This means that the silane molecule eliminates the electrical current leakage by isolating the graphene heat spreader and the electronic device. Consequently, the main source of the thermal conductance in this system is phonons as the thermal conductance due to the electrons contributes to the total thermal conductance by about 20% (Methods).

We have also investigated the in-plane thermal conductivity κ of the graphene film and its thermal resistance R with the functionalized substrate versus the equivalent molecule number density ρ . Both κ and R decay with the number density of the molecules ρ . In the limit of small number density [38], we consider the molecules as independent heat conductors connecting the film and the substrate. R agrees well with a reduced-model of parallel thermal resistors. Thus R decreases with the number of molecules. κ also decreases with the molecule number since the molecules increase the cross-plane phonon scattering in the graphene film. For larger ρ , the interactions among the molecules gain importance and R starts to deviate from the prediction of the parallel-thermal-resistor model, as shown in Figure 5. For large ρ , the thermal resistance R is lower than that without molecules. However κ remains enhanced

by a factor of $\approx 15\%$ compared to its value for the non-functionalized graphene substrate. The molecule density ρ effectively tunes the thermal conductivity of the supported graphene.

CONCLUSIONS

We address the long-standing problem of detrimental effect of covalent functionalization on the thermal conductivity of supported few-layer graphene. An unprecedented increase in the basal-plane thermal conductivity of supported graphene was achieved while improving the graphene-substrate’s thermal contact. Atomistic calculations show that the functionalization constrains the cross-plane scattering of low frequency phonons, which in turn enhances in-plane heat conduction of the bonded graphene film through phonon lifetime prolongation. Furthermore, we achieve a flexible tuning of the in-plane thermal conductivity of the supported graphene by adjusting the molecule density. Our atomistic calculations provide a microscopic insight and disclose the physics of phonon transport between two graphitic nanomaterials bonded with molecules. The detailed analysis reveals the intriguing role of molecular wires in controlling the heat transfer at the atomic-scale interface, which classical models fail to provide. Such a strategy is experimentally proven to be viable and important to the engineering of graphene electronics with improved heat transfer properties.

METHODS

Simulation setup. classical MD simulations were performed using LAMMPS [48]. The adaptive intermolecular reactive empirical bond order (AIREBO) potential [49] was used to simulate the graphene’s C-C interactions. The long-range electromagnetic and the short-range repulsive-attractive interactions in the molecule is taken into account through the van Beest, Kramer, and van Santen (BKS) potential. composed of Coulomb and Buckingham potentials. Periodic boundary conditions are applied in the in-plane directions and free boundary condition in the cross-plane direction of the graphene system. First, each super cell was relaxed at the simulation temperature to achieve zero in-plane stress. Then the systems were thermalized by using a Langevin heat bath. After the thermalization, MD runs with durations equal to 600 ps were carried out in the microcanonical ensemble to sample the temperature and heat flux to be used in the calculation of the thermal resistance and thermal

conductivity. Calculation details concerning the thermal resistance, thermal conductivity, phonon transmission and phonon relaxation time can be found in the Supporting Information Section III[29].

Ab initio calculations were carried out using the quantum chemistry DFT code SIESTA [53]. All systems were first geometrically optimized in isolation, with a generalized local-density approximations (LDA) within Ceperley-Alder version (CA), double-zeta polarized basis set, 0.01 eV/Å force tolerance and 250 Ry mesh cutoff. The relaxed atomic structures can be seen in Supplemental Figures (FIG.S3). Electron transmission coefficients were computed using the GOLLUM [52] code. To produce the conductance curves in Fig. (4), the transmission coefficient $T_{\text{el}}(E_F)$ was calculated for each relaxed junction geometry, by first obtaining the corresponding Hamiltonian and then overlapping matrices with SIESTA and double-zeta polarized basis set. To produce conductance-trace curves, the transmission coefficient $T_{\text{el}}(E_F)$ was calculated for each relaxed junction geometry and the conductance $G_{\text{el}}/G_0 = T_{\text{el}}(E_F)$ was obtained by evaluating $T_{\text{el}}(E_F)$ at the Fermi energy E_F .

Thermal conductance. Thermal conductance $G_{\text{th}} = G_e + G_{\text{ph}}$ where G_{ph} (G_e) is the thermal conductance due to the phonons (electrons). From the Phonon transmission $\Xi(E_{\text{ph}})$ the thermal conductance due to the the phonon could be calculated as $G_{\text{ph}}(T) = \int_0^\infty d\omega \left(-\frac{\partial f_{\text{BE}}}{\partial E}\right) \hbar\omega\Xi(\omega)/2\pi$. where ω is the frequency. T refers to the mean temperature of the system, f_{BE} is the Bose-Einstein phonon statistics. k_B and $\hbar$ represent the Boltzmann and the reduced Plancks constants, respectively. The thermal conductance due to the electrons [50, 51] could be calculated from the electron transmission coefficient T_{el} as $G_e(T) = \frac{L_0 L_2 - L_1^2}{hTL_0}$ where $L_n = \int_{-\infty}^\infty dE (E - E_F)^n T_{\text{el}}(E) \left(-\frac{\partial f_{\text{FD}}}{\partial E}\right)$ where f_{FD} is the Fermi-Dirac electron statistics.

Experimental method. (i) Sample Synthesis. Graphite (Sigma, 4g), H_2SO_4 (92 mL, 98%), NaNO_3 (2g) and KMnO_4 (12g) was used to prepare graphene oxide (GO) dispersion by following Hummers Method [47]. The obtained GO dispersion was reduced by L-ascorbic acid (LAA), polyvinyl alcohol (PVA) was also added for better suspension. The graphene-based film was prepared via vacuum filtration with polycarbonate filter paper with the pore size of 3 μm . The film thickness was controlled by the filtration volume and the graphene concentration in the suspension. After dissolving the filter paper in pure acetone, a freestanding graphene-based film was obtained. The thickness of the graphene-based film was measured as approximately 20 μm . Raman spectroscopy data of the GBF before and

after the spin-coating with FGO is shown in Supporting Information Section VII[29]. (ii) Functionalization. GO powder (20 mg) and Dicyclohexylcarbodiimide (DCC) (5 mg) were mixed with (3-Aminopropyl) triethoxysilane (APTES) (30 mL) by ultrasonication for 2h to produce a homogeneous suspension. Then the suspension was heated up to 100°C for 3h with continuous stirring to realize the functionalization. Fourier Transform Infrared Spectroscopy (FTIR) data provides evidence for the functionalization[29]. (iii) Transfer process. The graphene-based film was first transferred onto a thermal release tape, and then spin-coated [27] with the FGO layer at 4000 rpm for 2 min onto the film. The thermal release tape was removed by heating the device.

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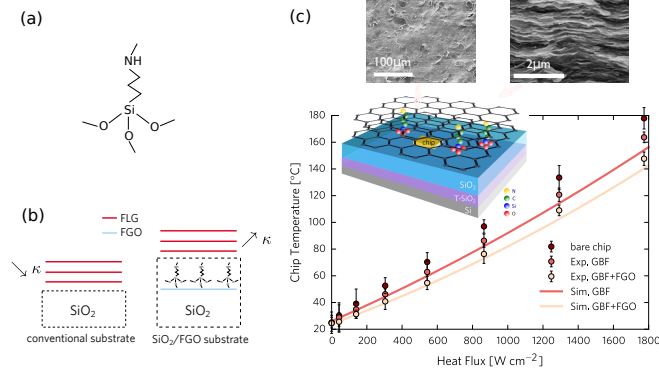


FIG. 1. (a) Sketch of the chemical bonds of the silane molecule. (b) Schematic of a graphene film on different supports. Left: Conventional silica substrate. Right: the proposed silica / functionalized graphene oxide substrate. (c) Measured (filled circles) and FEM simulated (lines) chip temperatures versus the in-plane heat fluxes dissipated in a bare chip, a chip covered by a GBF and a chip covered by a GBF with functionalized GO. (Inset) Schematic of the measurement setup. The chip is embedded in the SiO₂ substrate. T-SiO₂ stands for thermally-grown SiO₂. Scanning electron microscopy (SEM) image of the in-plane and the cross section of the GBF.

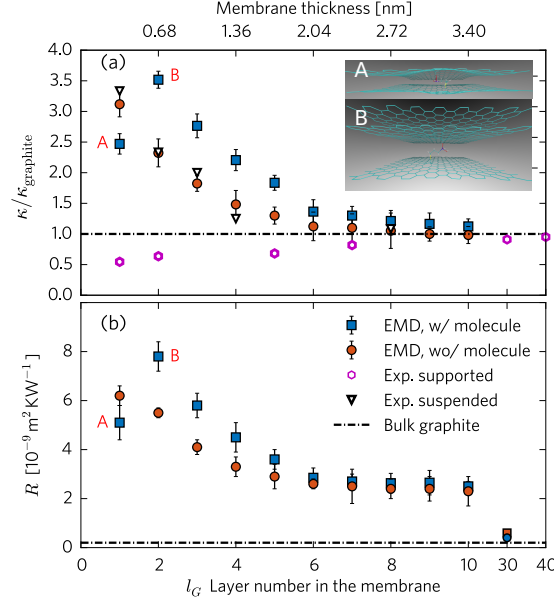


FIG. 2. (a) MD simulation results of in-plane thermal conductivity κ of the graphene film and (b) interfacial thermal resistance R between the FGO substrate and the graphene film versus the graphene layer number l_G in the film. The molecule density is $\rho = 0.081 \text{ nm}^{-2}$. Cases with (red open squares) and without (blue open circles) the molecule are compared. The values of thermal conductivity are normalized to that of the single-layer graphene. Inset A illustrates a saddlelike surface generated by the molecule for $l_G = 1$. Inset B shows that the saddlelike curvature disappears for $l_G \geq 1$. The measurements of suspended and supported graphene are from [7] and [8], respectively. The simulated (resp. measured) thermal conductivity is normalized with respect to that of the simulated (resp. measured) graphite, in order to allow for a reasonable comparison.

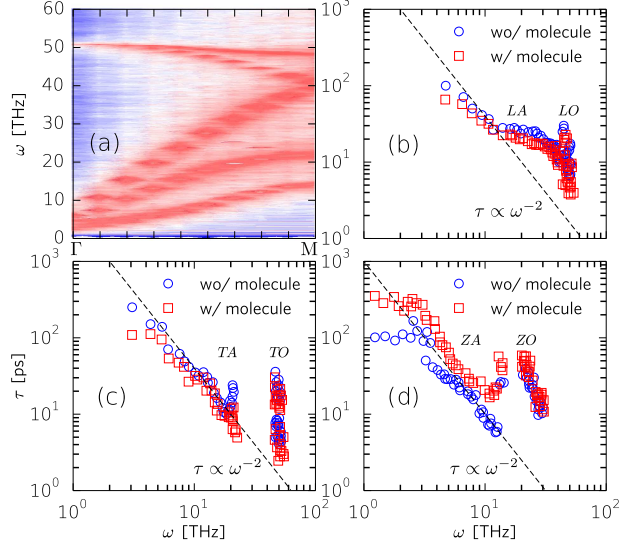


FIG. 3. (a) Phonon dispersion of the graphene film bonded to the FGO substrate from equilibrium MD simulations, for $\rho = 0.081 \text{ nm}^{-2}$ and $l_G=2$. (b), (c) and (d) Mode-wise phonon relaxation time for longitudinal modes including longitudinal acoustic (LA) and optical (LO) branches, for transverse modes including transverse acoustic (TA) and optical (TO) branches, and for flexural modes including flexural acoustic (ZA) and optical (ZO) branches, respectively. For low frequency phonons, τ follows the ω^{-2} scaling rule of the Umklapp processes at low frequency and high-temperature limits.

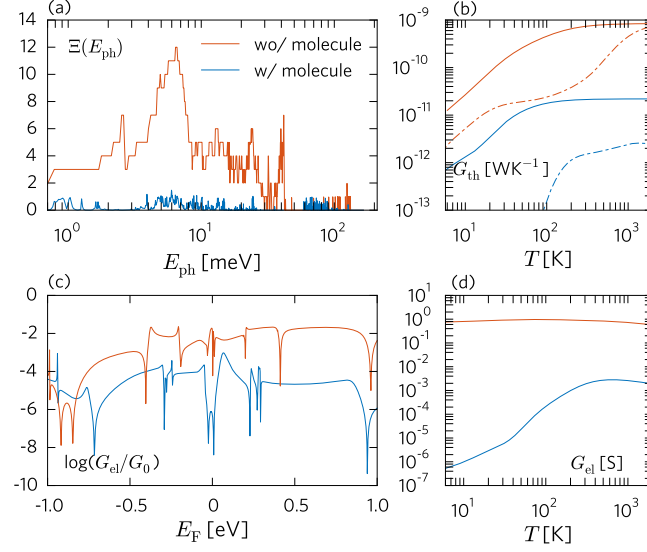


FIG. 4. (a) Phonon transmission $\Xi(E_{\text{ph}})$ versus phonon energy $E_{\text{ph}} = \hbar\omega$ (red curve) between two adjacent graphene layers and (blue curve) through the silane molecule bonding the two graphene layers. (b) Thermal conductances $G_{\text{th}} = G_{\text{e}} + G_{\text{ph}}$ contributed by phonons G_{ph} (solid lines) and electrons G_{e} (dashed lines) versus temperature for the two cases. (c) Electron transmission $T_{\text{el}} = G_{\text{el}}/G_0$ versus Fermi energy E_{F} between two adjacent graphene layers and (blue curve) through the silane molecule bonding the two graphene layers. (d) Electrical conductances $G_{\text{el}}(T)$ versus temperature for the two cases.

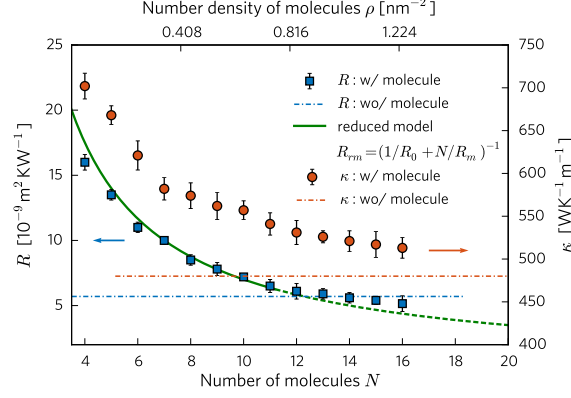


FIG. 5. Thermal conductivity κ (red open circles) of the graphene film and its thermal resistance R (blue open squares) with the functionalized substrate versus the equivalent molecule number density ρ . (Green line) Resistance R_{rm} predicted by a reduced-model of parallel thermal resistors is to compare with the MD results for small ρ . $R_{rm} = (1/R_0 + N/R_m)^{-1}$ where R_0 is the thermal resistance between two adjacent graphene layers and R_m is the additional resistance induced by a single molecule. The values of R_0 and R_m are determined in MD simulations: $R_0 = 0.203 \text{ mm}^2\text{KW}^{-1}$ and $R_m = 0.069 \text{ mm}^2\text{KW}^{-1}$. Red and blue dashed lines represent, respectively, κ and R without the interconnecting molecule between at the film-substrate interface.